High-Power Diode Laser Technology and Applications VIII

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Editor

25–26 January 2010
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 7583
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Please use the following format to cite material from this book:


ISSN 0277-786X
ISBN 9780819479792

Published by

SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
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